



# P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$ Max.	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)						
- 20	0.033 at V <sub>GS</sub> = - 4.5 V	- 12							
	0.042 at V <sub>GS</sub> = - 2.5 V	- 12	18 nC						
	0.055 at V <sub>GS</sub> = - 1.8 V	- 12							

# PowerPAK SC-70-6L-Single 2.05 mm 2.05 mm

#### **Ordering Information:**

SiA461DJ-T1-GE3 (Lead (Pb)-free and Halogen free)

#### **FEATURES**

- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
  - Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

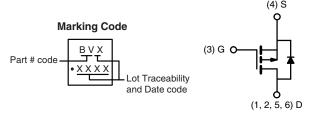


RoHS HALOGEN

FREE

#### **APPLICATIONS**

- Smart Phones, Tablet PCs, Mobile Computing
  - Battery Switch
  - Charger Switch
  - Load Switch



P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATIN</b>	IGS (T <sub>A</sub> = 25 °C	, unless othe	erwise noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	- 20	V	
Gate-Source Voltage		$V_{GS}$	± 8	V	
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 12 <sup>a</sup>		
Continuous Diam Current (1) = 130 °C)	T <sub>A</sub> = 25 °C		- 8.3 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	1	- 6.6 <sup>b, c</sup>	A	
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	- 20		
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 2.8 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		17.9		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	$P_{D}$	11.4	w	
Maximum Tower Dissipation	T <sub>A</sub> = 25 °C	1 '0 [	3.4 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	1	2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperatur	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera	ature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS										
Parameter		Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	$R_{thJA}$	29	37	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	5.5	7	O/ V V					

### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

Document Number: 63838 S12-0539-Rev. A, 12-Mar-12 For more information please contact: pmostechsupport@vishav.com

# SiA461DJ

# Vishay Siliconix



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			٧			
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 18		m\//°C			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	ι <sub>D</sub> = - 250 μΑ		3		mV/°C			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 0.4		- 1	V			
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 \text{ °C}$			- 1 - 10	μΑ			
On Ctata Drain Currenta	ln()	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20		- 10	Α			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5.2 A	- 20	0.005	0.000				
	В	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5.2 A V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 4.8 A		0.025	0.033				
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -4.6 \text{ A}$ $V_{GS} = -1.8 \text{ V}, I_D = -2 \text{ A}$		0.030	0.042	Ω			
		-		0.040	0.055				
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = -6 \text{ V}, I_{D} = -5.2 \text{ A}$		20		S			
Dynamic <sup>b</sup>	_			1	T				
Input Capacitance	C <sub>iss</sub>			1300					
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		210		pF			
Reverse Transfer Capacitance	C <sub>rss</sub>			180					
Total Gate Charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_{D} = -5.2 \text{ A}$		30	45	nC			
Total date onlarge	$Q_g$			18	27				
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.2 \text{ A}$		2.1					
Gate-Drain Charge	$Q_{gd}$	ı		4.8					
Gate Resistance	$R_g$	f = 1 MHz		6		Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			20	30				
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_{L} = 2.4 \Omega$		22	35				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -4.2 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		50	75				
Fall Time	t <sub>f</sub>			20	30				
Turn-On Delay Time	t <sub>d(on)</sub>			10	15	ns			
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_1 = 2.4 \Omega$		12	25	<del>-</del>			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -4.2 \text{ A}, V_{GEN} = -8 \text{ V}, R_q = 1 \Omega$		50	75				
Fall Time t <sub>f</sub>		j		15	25	1			
Drain-Source Body Diode Characteristic					<u> </u>				
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	Ι.			
Pulse Diode Forward Current <sup>a</sup>		•			- 20	A			
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = - 4.2 A		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	<u> </u>		45	70	ns			
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			40	60	nC			
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = -4.2 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		23	- 55	ns			
	t <sub>b</sub>			22	ļ				

#### Notes:

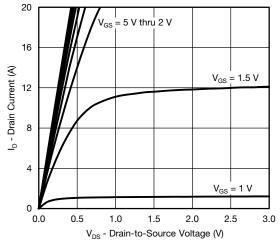
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$ 

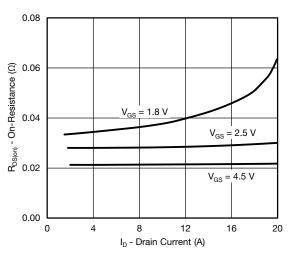
b. Guaranteed by design, not subject to production testing.



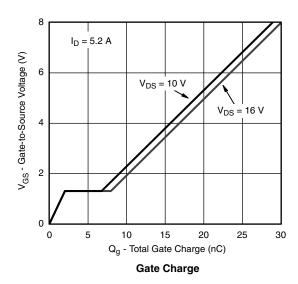
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

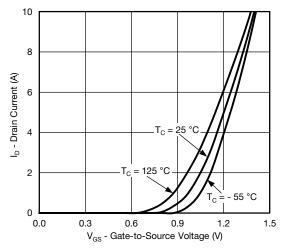


#### **Output Characteristics**

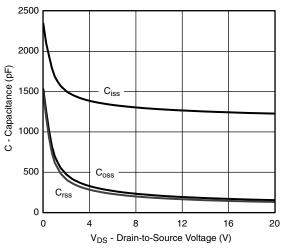


On-Resistance vs. Drain Current and Gate Voltage

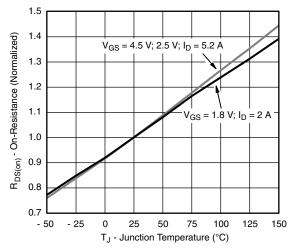




**Transfer Characteristics** 



Capacitance

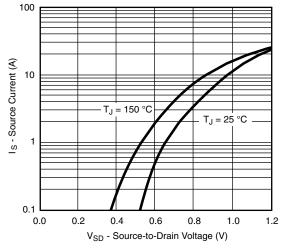


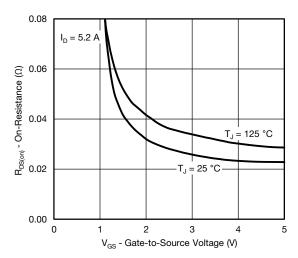
On-Resistance vs. Junction Temperature

# SiA461DJ

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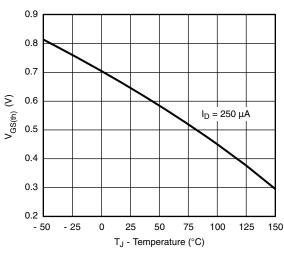
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

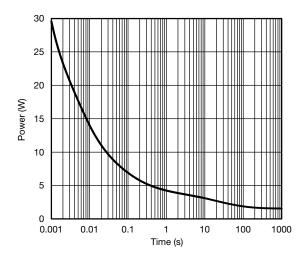




#### Source-Drain Diode Forward Voltage

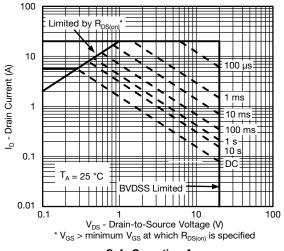
On-Resistance vs. Gate-to-Source Voltage





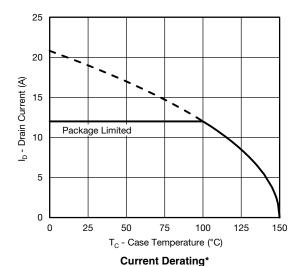
Threshold Voltage

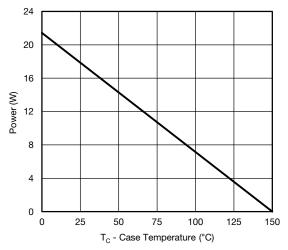
Single Pulse Power





# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





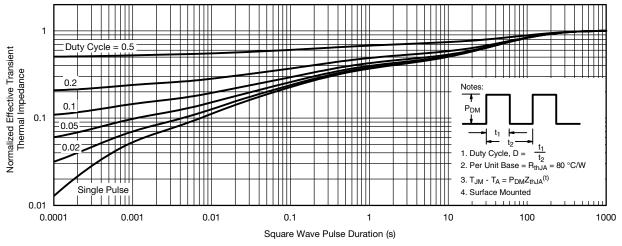
Power, Junction-to-Case

<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

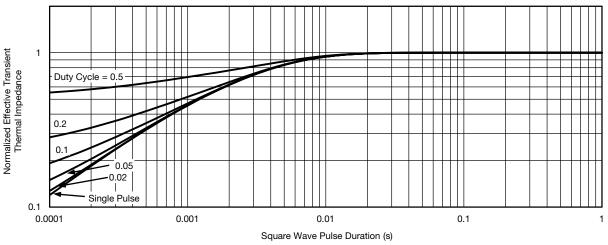
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## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



## Normalized Thermal Transient Impedance, Junction-to-Ambient



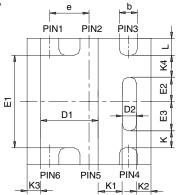
Normalized Thermal Transient Impedance, Junction-to-Case

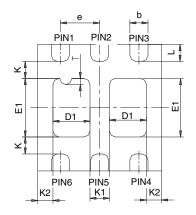
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63838.





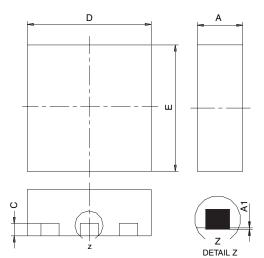
# PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
   Package outline exclusive of mold flash and metal burr
   Package outline inclusive of plating

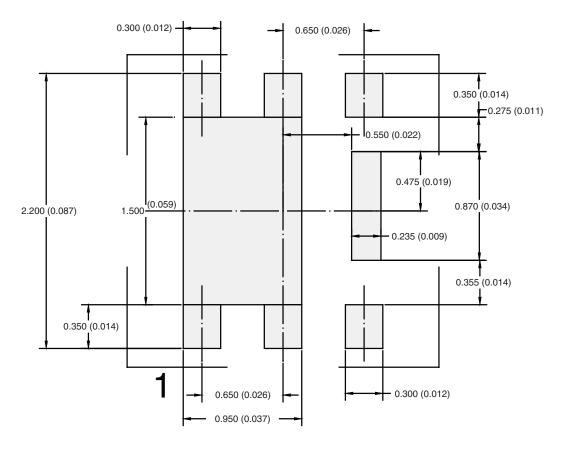
	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS	INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC			
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	١	0.009 TYP			0.252 TYP			0.010 TYP			
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP		0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Bey C 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000

# AMEYA360 Components Supply Platform

# **Authorized Distribution Brand:**

























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